

**关键参数**
**Key Parameters**

$V_{CES}$		750	V
$V_{CE(sat)}$	Typ.	1.70	V
$I_C$	Max.	400	A
$I_{C(RM)}$	Max.	800	A

**典型应用**
**Typical Applications**

● 电动汽车应用	Automotive applications
● 混合动力/纯电动车	Hybrid/Electrical vehicles
● 电机驱动	Motor drives

**特点**
**Features**

● 铜基板	Cu baseplate
● 增强型氧化铝衬板	Enhanced $Al_2O_3$ substrates
● 750V 额定电压	Blocking Voltage 750V
● 高电流密度	High current density

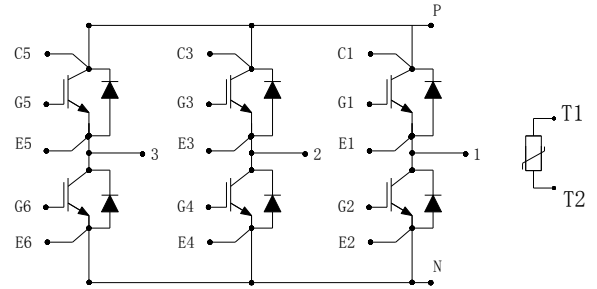
**电路结构**
**Circuit Configuration**


图 1. 电路结构

Fig. 1 Circuit configuration

**模块外形**
**Module Appearance**


图 2. 模块外形

Fig. 2 Module appearance

**模块标签说明**
**Module Label Code Instruction**


数据位置 Data position	数据内容 Content of data
1—8	模块批次号 Module batch number
9—12	模块序列号 Module serial number

**最大额定值**
**Absolute Maximum Ratings**

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	数值 Value	单位 Unit
$V_{CES}$	集电极-发射极电压 Collector-emitter voltage	$V_{GE} = 0V, T_C = 25^\circ C$	750	V
$V_{GES}$	栅极-发射极电压 Gate-emitter voltage	$T_C = 25^\circ C$	$\pm 20$	V
$I_C$	集电极电流 Collector-emitter current	$T_C = 65^\circ C, T_{vj\ max} = 175^\circ C$	400	A
$I_{C(PK)}$	集电极峰值电流 Peak collector current	$t_P = 1ms$	800	A
$P_{max}$	晶体管部分最大损耗 Max. transistor power dissipation	$T_C = 25^\circ C, T_{vj\ max} = 175^\circ C$	1250	W
$\rho_t$	二极管 $\rho_t$ 值 Diode $\rho_t$	$V_R = 0V, t_P = 10ms, T_{vj} = 150^\circ C$	8500	A <sup>2</sup> s
$V_{isol}$	绝缘电压(模块) Isolation voltage – per module	短接所有端子, 端子与基板间施加电压 (Commoned terminals to baseplate), AC RMS, 1 min, 50Hz, $T_C = 25^\circ C$	2500	V

**热和机械数据**
**Thermal & Mechanical Data**

参数 Symbol	说明 Explanation	值 Value	单位 Unit
爬电距离 Creepage distance	端子-散热器 Terminal to heatsink	12	mm
	端子-端子 Terminal to terminal	6.1	mm
绝缘间隙 Clearance	端子-散热器 Terminal to heatsink	12	mm
	端子-端子 Terminal to terminal	6.1	mm
相对漏电起痕指数 CTI (Comparativetrackingindex)		>200	

**热和机械数据**
**Thermal & Mechanical Data**

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$R_{th(J-C)}$ IGBT	IGBT 结壳热阻 Thermal resistance – IGBT				120	K / kW
$R_{th(J-C)}$ Diode	二极管结壳热阻 Thermal resistance – Diode				200	K / kW
$R_{th(C-H)}$ IGBT	接触热阻(IGBT) Thermal resistance – case to heatsink (IGBT)	安装力矩 5Nm, 导热脂 1W/m·°C Mounting torque 5Nm, with mounting grease 1W/m·°C		80		K / kW
$R_{th(C-H)}$ Diode	接触热阻(Diode) Thermal resistance – case to heatsink (Diode)	安装力矩 5Nm, 导热脂 1W/m·°C Mounting torque 5Nm, with mounting grease 1W/m·°C		85		K / kW
$T_{vj\ op}$	工作结温 Operating junction temperature	IGBT 部分 ( IGBT )	-40		150	°C
		二极管部分( Diode )	-40		150	°C
$T_{stg}$	存储温度 Storage temperature range		-40		125	°C
$M$	安装力矩 Screw torque	安装紧固用– M5 Mounting - M5	3		6	Nm
		电路互连用– M6 Electrical connections - M6	3		6	Nm

**热敏电阻数据**
**NTC-Thermistor Data**

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$R_{25}$	额定电阻值 Rated resistance	$T_C = 25\ ^\circ\text{C}$		5		kΩ
$\Delta R/R$	R100 偏差 Deviation of R100	$T_C = 100\ ^\circ\text{C}, R_{100}=493\Omega$	-5		5	%
$P_{25}$	耗散功率 Power dissipation	$T_C = 25\ ^\circ\text{C}$			20	mW
$B_{25/50}$	B-值 B-value	$R_2 = R_{25}\exp [B_{25/50}(1/T_2 - 1/(298.15\text{ K}))]$		3375		K
$B_{25/80}$	B-值 B-value	$R_2 = R_{25}\exp [B_{25/80}(1/T_2 - 1/(298.15\text{ K}))]$		3411		K
$B_{25/100}$	B-值 B-value	$R_2 = R_{25}\exp [B_{25/100}(1/T_2 - 1/(298.15\text{ K}))]$		3433		K

**电特性值**
**Electrical Characteristics**

 除非特别声明，否则  $T_C = 25\text{ }^\circ\text{C}$ 
 $T_C = 25\text{ }^\circ\text{C}$  unless otherwise stated

符号 Symbol	参数名称 Parameter	条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$I_{CES}$	集电极截止电流 Collector cut-off current	$V_{GE} = 0V, V_{CE} = V_{CES}$			1	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 125\text{ }^\circ\text{C}$			10	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 150\text{ }^\circ\text{C}$			15	mA
$I_{GES}$	栅极漏电流 Gate leakage current	$V_{GE} = \pm 20V, V_{CE} = 0V$			0.5	$\mu\text{A}$
$V_{GE(TH)}$	栅极-发射极阈值电压 Gate threshold voltage	$I_C = 10\text{mA}, V_{GE} = V_{CE}$	5.30	5.90	6.50	V
$V_{CE(sat)}^{(*1)}$	集电极-发射极饱和电压 Collector-emitter saturation voltage	$V_{GE} = 15V, I_C = 400A$		1.70	2.10	V
		$V_{GE} = 15V, I_C = 400A, T_{vj} = 125\text{ }^\circ\text{C}$		1.95		V
		$V_{GE} = 15V, I_C = 400A, T_{vj} = 150\text{ }^\circ\text{C}$		2.00		V
$I_F$	二极管正向直流电流 Diode forward current	DC		400		A
$I_{FRM}$	二极管正向重复峰值电流 Diode peak forward current	$t_p = 1\text{ms}$		800		A
$V_F^{(*1)}$	二极管正向电压 Diode forward voltage	$I_F = 400A, V_{GE} = 0$		1.60	2.00	V
		$I_F = 400A, V_{GE} = 0, T_{vj} = 125\text{ }^\circ\text{C}$		1.70		V
		$I_F = 400A, V_{GE} = 0, T_{vj} = 150\text{ }^\circ\text{C}$		1.70		V
$I_{SC}$	短路电流 Short circuit current	$T_{vj} = 150\text{ }^\circ\text{C}, V_{CC} = 400V,$ $V_{GE} \leq 15V, t_p \leq 6\mu\text{s},$ $V_{CE(max)} = V_{CES} - L^{(*2)} \times di/dt,$ IEC 6074-9		1600		A

**注意:** 1. (\*1) 表示该参数的测试点为辅助母排端子 (\*1) indicates it is measured at the auxiliary busbar terminal),

**Note:** 2. (\*2) 表示  $L$  是电路杂散电感加上  $L_M$  (\*2) indicates  $L$  is the circuit stray inductance plus  $L_M$ ).

**电特性值**
**Electrical Characteristics**

 除非特别声明，否则  $T_C = 25\text{ }^\circ\text{C}$ 
 $T_C = 25\text{ }^\circ\text{C}$  unless otherwise stated

符号 Symbol	参数名称 Parameter	条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$C_{ies}$	输入电容 Input capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		33		nF
$Q_g$	栅极电荷 Gate charge	$\pm 15V$		2.5		$\mu C$
$C_{res}$	反向传输电容 Reverse transfer capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		0.5		nF
$L_M$	模块电感 Module inductance			30		nH
$R_{INT}$	内阻 Internal transistor resistance			1		m $\Omega$

**电特性值**
**Electrical Characteristics**

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit	
$t_{d(off)}$	关断延迟时间 Turn-off delay time	$I_C = 400A,$ $V_{CE} = 400V,$ $V_{GE} = \pm 15V,$ $R_{G(OFF)} = 1.8\Omega,$ $L_S = 65nH,$ $dv/dt = 6000V/us$ ( $T_{vj} = 150^\circ C$ ).	$T_{vj} = 25^\circ C$	515		ns	
			$T_{vj} = 125^\circ C$	545			
			$T_{vj} = 150^\circ C$	555			
$t_f$	下降时间 Fall time		$T_{vj} = 25^\circ C$		60		ns
			$T_{vj} = 125^\circ C$		75		
			$T_{vj} = 150^\circ C$		80		
$E_{OFF}$	关断损耗 Turn-off energy loss		$T_{vj} = 25^\circ C$		16.0		mJ
			$T_{vj} = 125^\circ C$		18.0		
			$T_{vj} = 150^\circ C$		23.0		
$t_{d(on)}$	开通延迟时间 Turn-on delay time	$T_{vj} = 25^\circ C$		430		ns	
		$T_{vj} = 125^\circ C$		430			
		$T_{vj} = 150^\circ C$		430			
$t_r$	上升时间 Rise time	$T_{vj} = 25^\circ C$		80		ns	
		$T_{vj} = 125^\circ C$		85			
		$T_{vj} = 150^\circ C$		85			
$E_{ON}$	开通损耗 Turn-on energy loss	$T_{vj} = 25^\circ C$		5.5		mJ	
		$T_{vj} = 125^\circ C$		6.5			
		$T_{vj} = 150^\circ C$		7.0			
$Q_{rr}$	二极管反向恢复电荷 Diode reverse recovery charge	$T_{vj} = 25^\circ C$		25		$\mu C$	
		$T_{vj} = 125^\circ C$		40			
		$T_{vj} = 150^\circ C$		44			
$I_{rr}$	二极管反向恢复电流 Diode reverse recovery current	$T_{vj} = 25^\circ C$		235		A	
		$T_{vj} = 125^\circ C$		260			
		$T_{vj} = 150^\circ C$		270			
$E_{rec}$	二极管反向恢复损耗 Diode reverse recovery energy	$T_{vj} = 25^\circ C$		8.5		mJ	
		$T_{vj} = 125^\circ C$		13.5			
		$T_{vj} = 150^\circ C$		14.5			

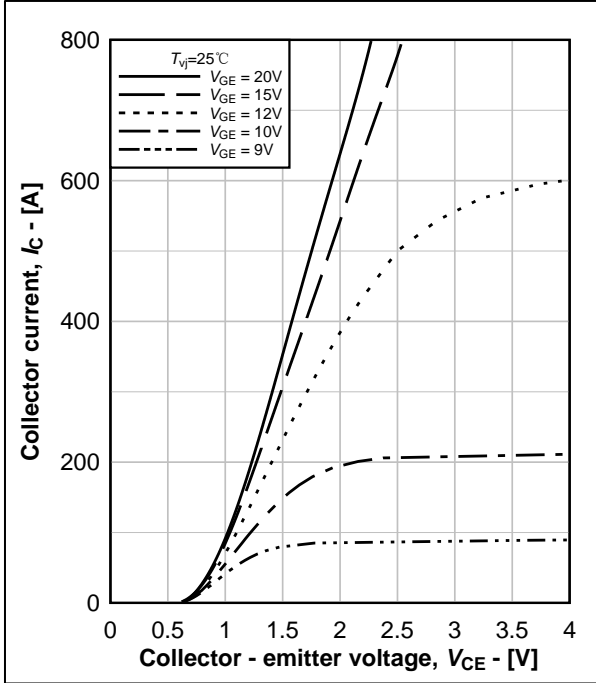


图 3. IGBT 输出特性典型曲线,  $I_C = f(V_{CE})$

Fig.3 Typical IGBT output characteristics,  $I_C = f(V_{CE})$

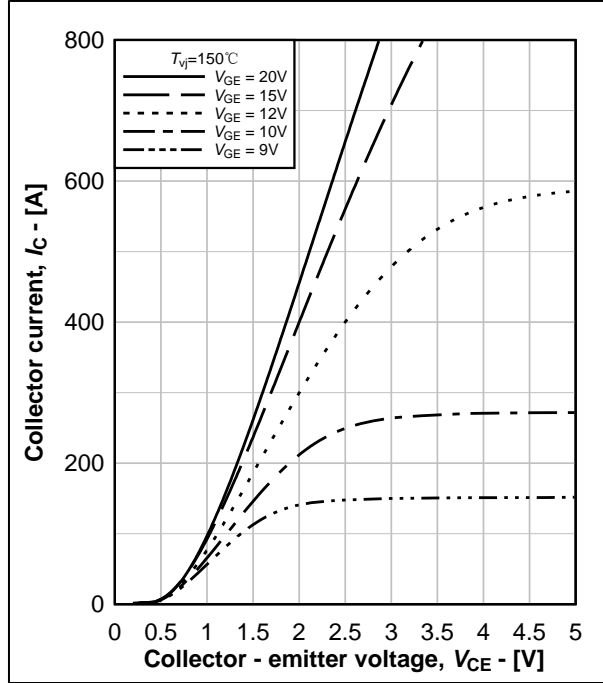


图 4. IGBT 输出特性典型曲线,  $I_C = f(V_{CE})$

Fig.4 Typical IGBT output characteristics,  $I_C = f(V_{CE})$

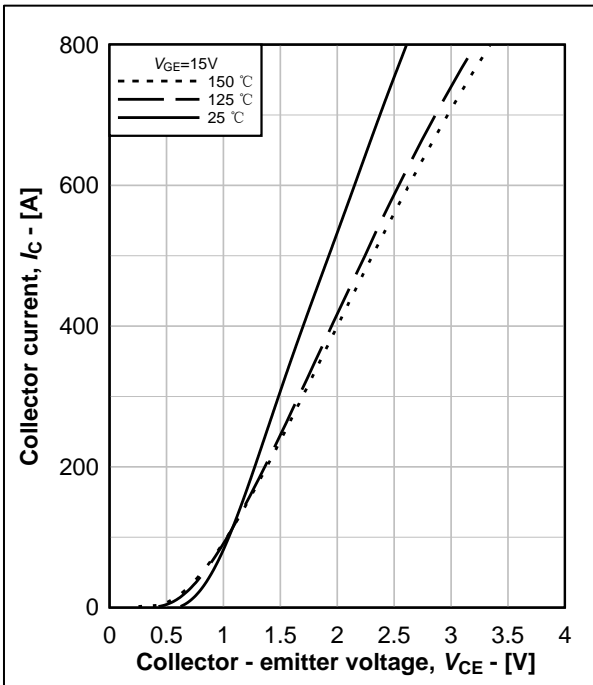


图 5. IGBT 输出特性典型曲线,  $I_C = f(V_{CE})$

Fig.5 Typical IGBT output characteristics,  $I_C = f(V_{CE})$

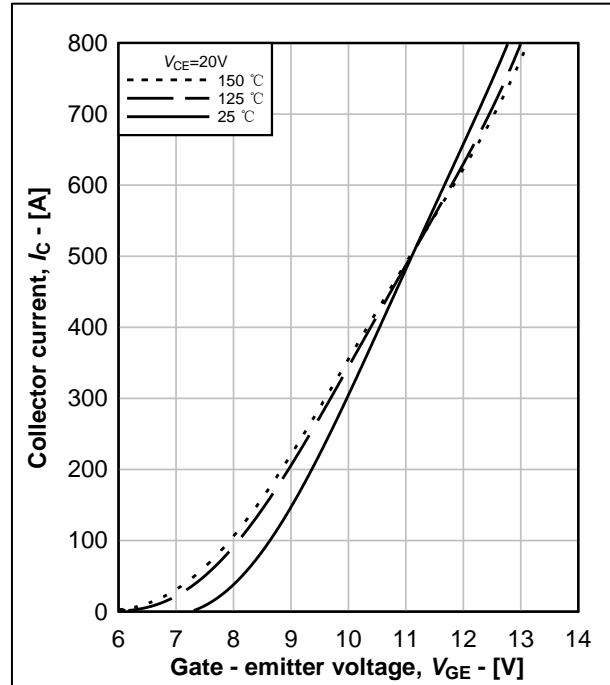


图 6. IGBT 传输特性典型曲线,  $I_C = f(V_{GE})$

Fig.6 Typical IGBT transfer characteristics,  $I_C = f(V_{GE})$

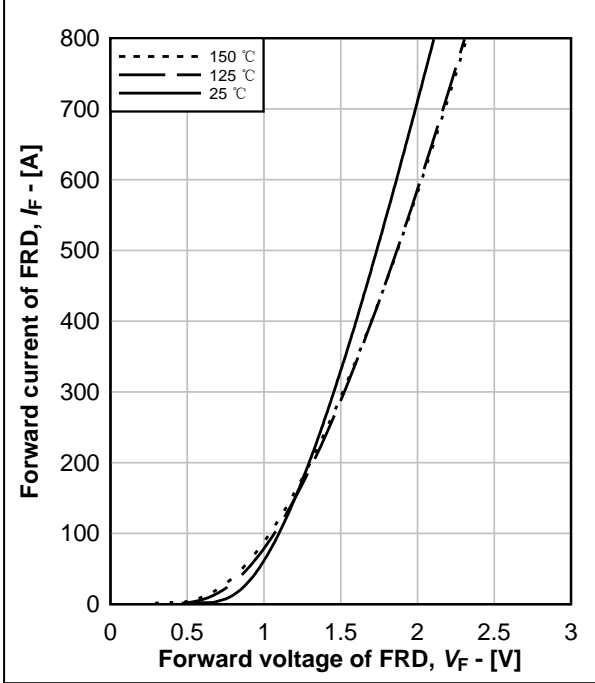


图 7. FRD 输出特性典型曲线,  $I_F = f(V_F)$

Fig.7 Typical FRD output characteristics,  $I_F = f(V_F)$

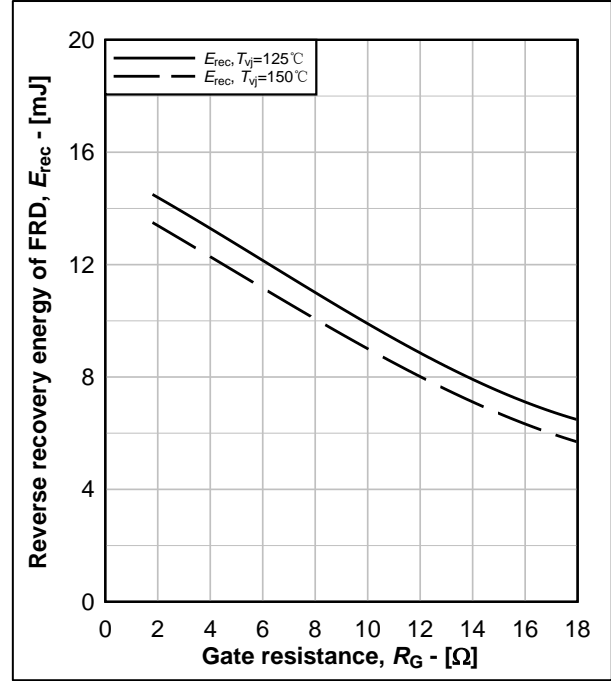


图 8. FRD 反向恢复能耗典型曲线,  $E_{rec} = f(R_G)$

Fig.8 Typical FRD  $E_{rec}$ ,  $E_{rec} = f(R_G)$

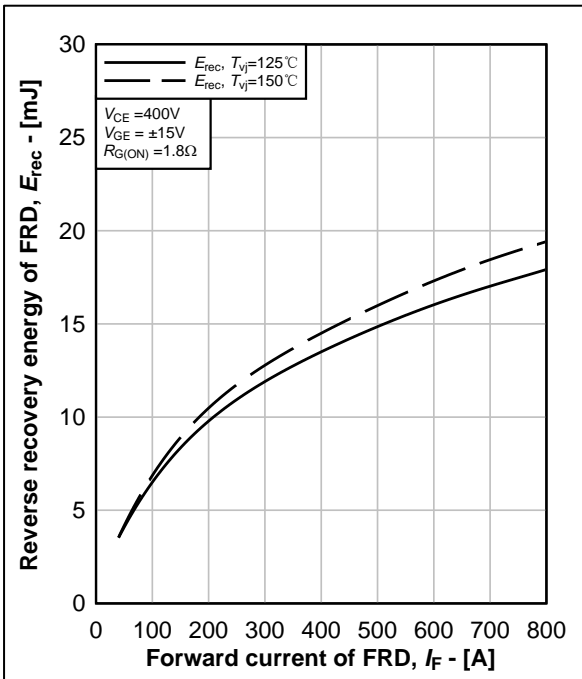


图 9. FRD 反向恢复能耗典型曲线,  $E_{rec} = f(I_F)$

Fig.9 Typical FRD  $E_{rec}$ ,  $E_{rec} = f(I_F)$

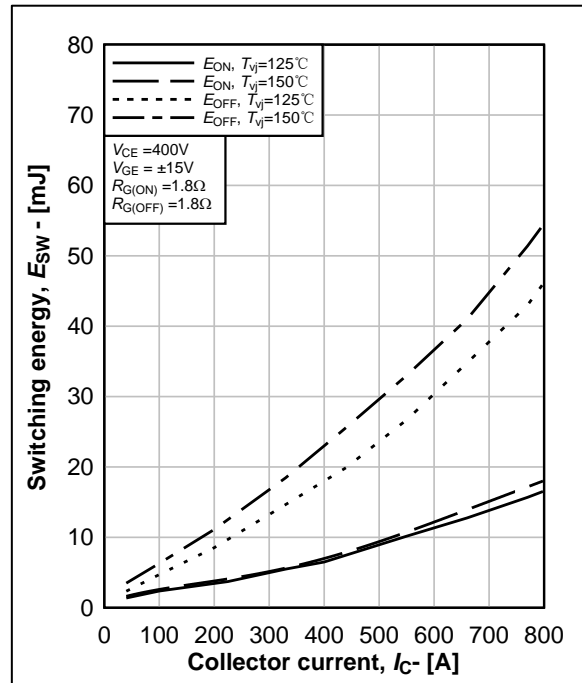


图 10. IGBT 开关能耗典型曲线,  $E_{on} = f(I_C)$ ,  $E_{off} = f(I_C)$

Fig.10 Typical IGBT switching energy,  $E_{on} = f(I_C)$ ,  $E_{off} = f(I_C)$



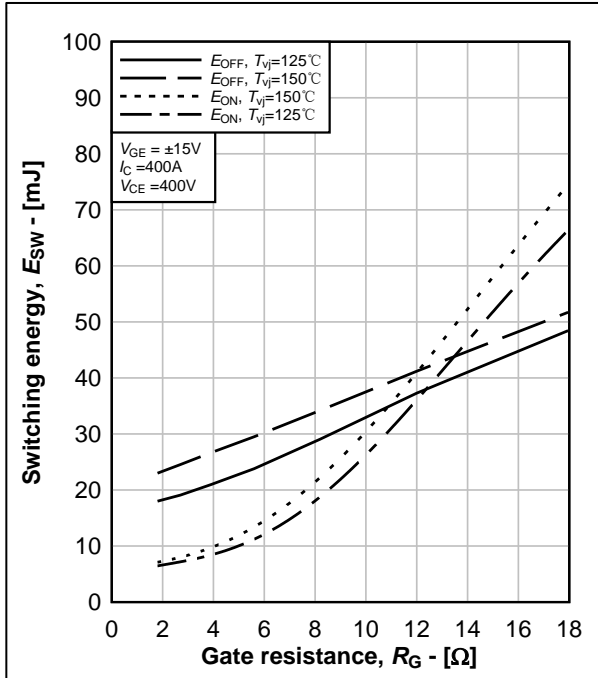

 图 11. IGBT 开关能耗典型曲线,  $E_{on} = f(R_G)$ ,  $E_{off} = f(R_G)$ 

Fig.11 Typical IGBT switching energy,

$$E_{on} = f(R_G), E_{off} = f(R_G)$$

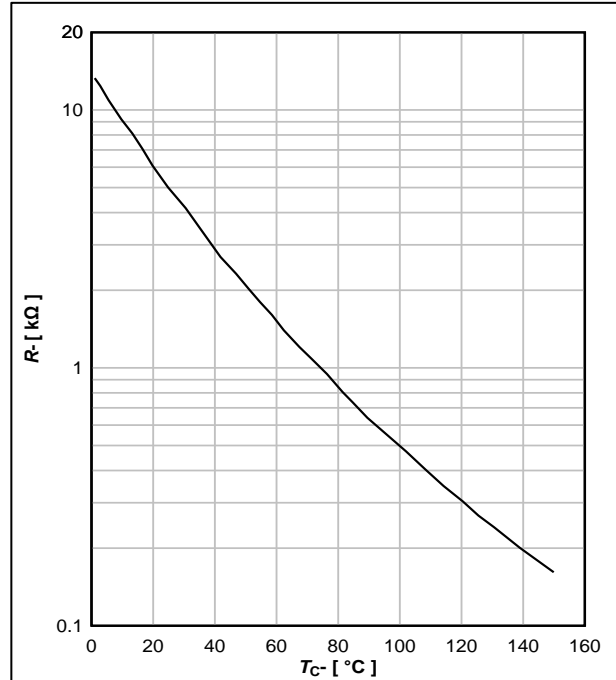

 图 12. 热敏电阻典型特性曲线,  $R = f(T_C)$ 

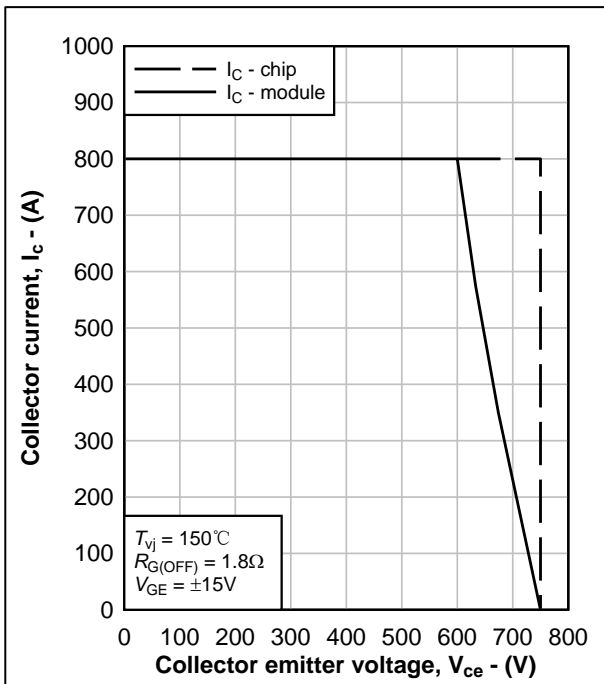
 Fig.12 Typical NTC thermistor characteristic,  $R = f(T_C)$ 

 图 13. IGBT 反偏安全工作区,  $I_C = f(V_{CE})$ 

Fig.13 Reverse bias safe operating area of IGBT,

$$I_C = f(V_{CE})$$

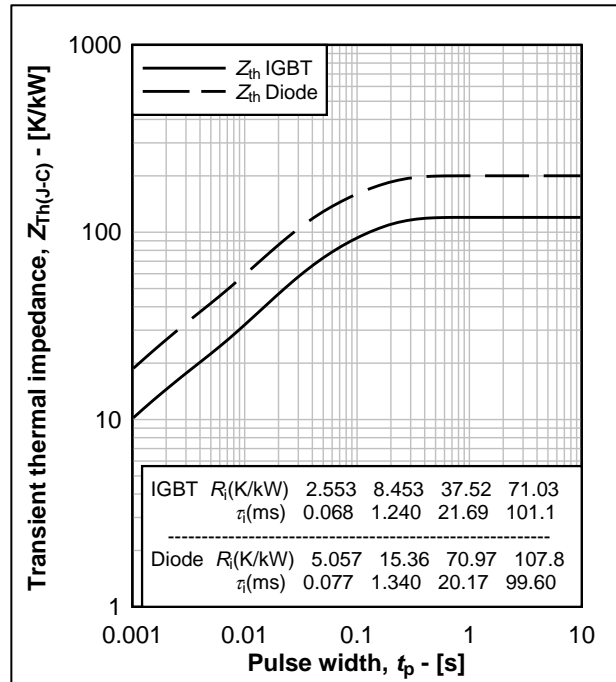
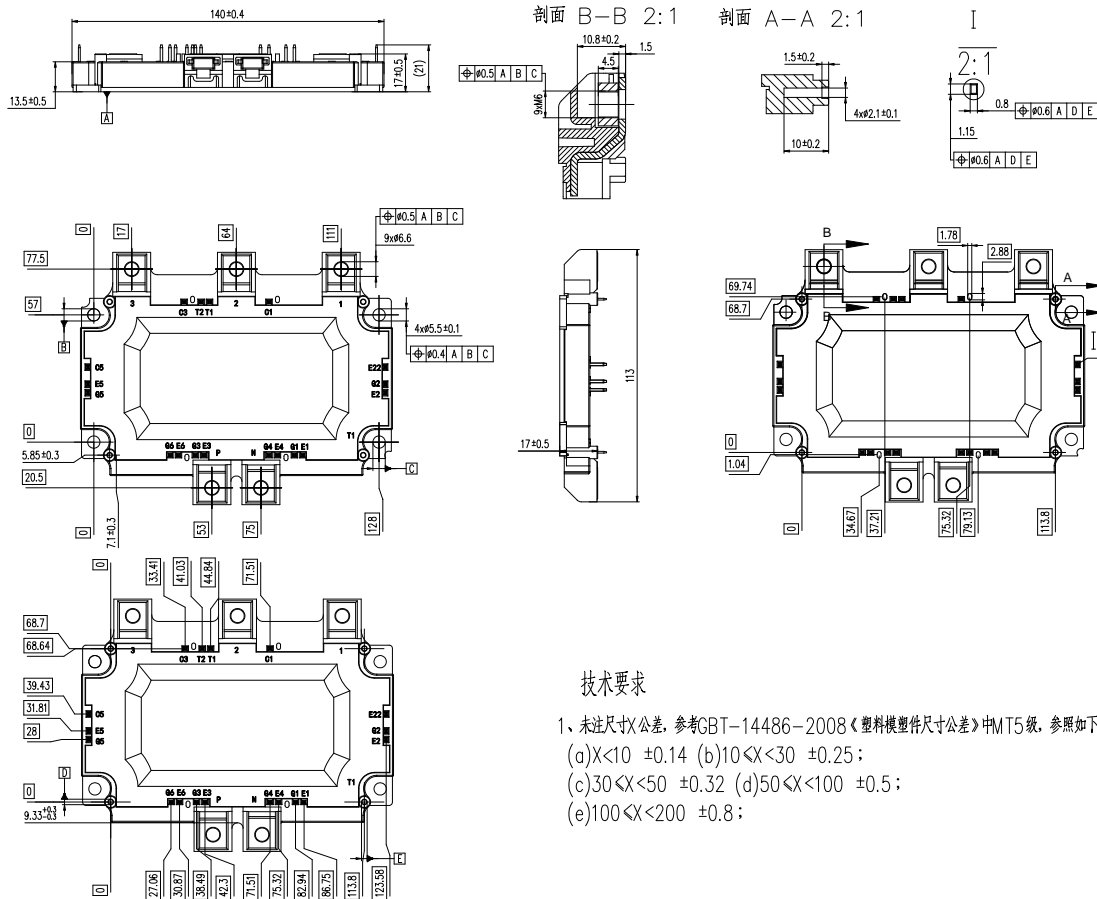

 图 14. 瞬态热阻抗曲线,  $Z_{Th(J-F)} = f(t_p)$ 

 Fig.14 Transient thermal impedance,  $Z_{Th(J-F)} = f(t_p)$


**技术要求**

- 1、未注尺寸公差，参考GB/T-14486-2008《塑料模塑件尺寸公差》中MT5级，参照如下：  
 (a) $X < 10 \pm 0.14$  (b) $10 < X < 30 \pm 0.25$ ；  
 (c) $30 < X < 50 \pm 0.32$  (d) $50 < X < 100 \pm 0.5$ ；  
 (e) $100 < X < 200 \pm 0.8$ ；

重量 Weight: 485g

模块外观类型 Module outline code: S0

图 15. 模块外观尺寸

Fig. 15 Module outlines

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